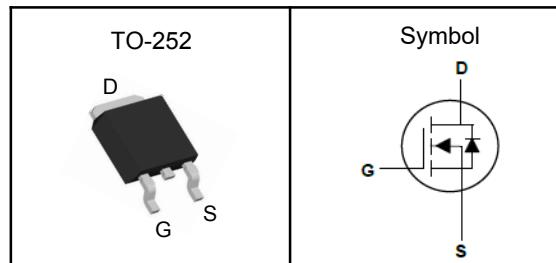


650 Super Junction Power MOSFET

Features

- Low drain-source on-resistance: $R_{DS(ON)}=1\Omega(\text{typ})$
- Easy to control gate switching
- Enhancement mode: $V_{th} = 2.5$ to $4.0V$
- 100% avalanche tested
- RoHS compliant

Pin Description



Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger, Lighting.

V_{DSS}	650	V
$R_{DS(ON)-Typ}$	1000	$\text{m}\Omega$
I_D	5	A

Absolute Maximum Ratings ($T_J=25^\circ\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit	
V_{DSS}	Drain-Source Voltage	650	V	
V_{GSS}	Gate-Source Voltage	± 30	V	
T_J	Maximum Junction Temperature	-55 to 150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$	
E_{AS}	Single Pulse Avalanche Energy ^③	51.2	mJ	
$I_{DM}^{①}$	Pulse Drain Current Tested	12	A	
I_D	Continuous Drain Current	$T_c=25^\circ\text{C}$	5	A
P_D	Maximum Power Dissipation	$T_c=25^\circ\text{C}$	116	W

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ^①	62.5	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ^①	1.07	$^\circ\text{C}/\text{W}$

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150°C .

Note ③ : Surface Mounted on 1in² FR-4 board with 1oz.

650 Super Junction Power MOSFET

Electrical Characteristics ($T_J=25^\circ\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_D=1\text{mA}$	650	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=650\text{V}$, $V_{\text{GS}}=0\text{V}$	---	---	1	μA
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$, $I_D=0.8\text{mA}$	2.5	---	4.0	V
I_{GSS}	Gate Leakage Current	$V_{\text{GS}}=\pm30\text{V}$, $V_{\text{DS}}=0\text{V}$	---	---	±100	nA
$R_{\text{DS(ON)}}$	Drain-Source On-state Resistance	$V_{\text{GS}}=10\text{V}$, $I_D=2\text{A}$	---	1000	1200	$\text{m}\Omega$
Dynamic Characteristics^⑤						
C_{iss}	Input Capacitance	$V_{\text{GS}}=0\text{V}$, $V_{\text{DS}}=50\text{V}$, Freq.=1MHz	---	270	---	pF
C_{oss}	Output Capacitance		---	50	---	
C_{rss}	Reverse Transfer Capacitance		---	2.7	---	
$T_{\text{d(on)}}$	Turn-on Delay Time	$V_{\text{DD}}=400\text{V}$, $R_G=10\Omega$, $I_D=4\text{A}$	---	12	---	nS
T_r	Turn-on Rise Time		---	25	---	
$T_{\text{d(off)}}$	Turn-off Delay Time		---	29	---	
T_f	Turn-off Fall Time		---	25	---	
Q_g	Total Gate Charge	$V_{\text{DS}}=520\text{V}$, $V_{\text{GS}}=10\text{V}$, $I_D=4\text{A}$	---	9	---	nC
Q_{gs}	Gate-Source Charge		---	2.6	---	
Q_{gd}	Gate-Drain Charge		---	3.8	---	
Source-Drain Characteristics ($T_J=25^\circ\text{C}$)						
V_{SD}	Diode Forward Voltage ^②	$V_{\text{GS}}=0\text{V}$, $I_s=4\text{A}$, $T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_s=4\text{A}$, $V_{\text{DD}}=520\text{V}$ di/ $dt=100\text{A}/\mu\text{s}$, $T_J=25^\circ\text{C}$	---	209	---	nS
Q_{rr}	Reverse Recovery Charge		---	1.5	---	nC

Note ④ : Pulse test (pulse width $\leq300\text{us}$, duty cycle $\leq2\%$).

Note ⑤ : Guaranteed by design, not subject to production testing.

650 Super Junction Power MOSFET

Typical Characteristics

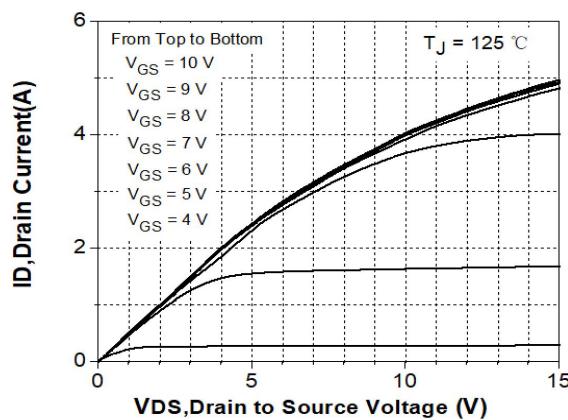


Figure 1. On-Region Characteristics

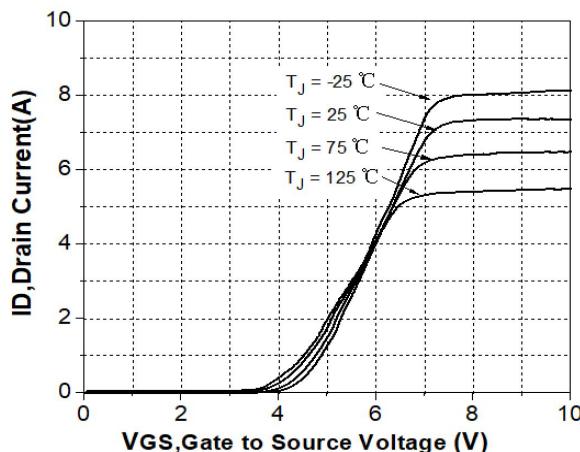


Figure 2. Transfer Characteristics

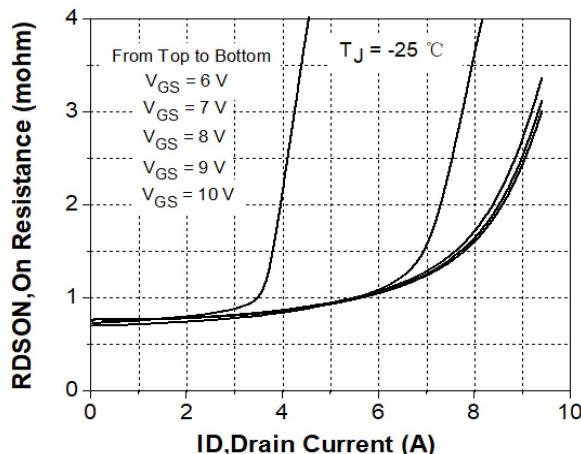


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

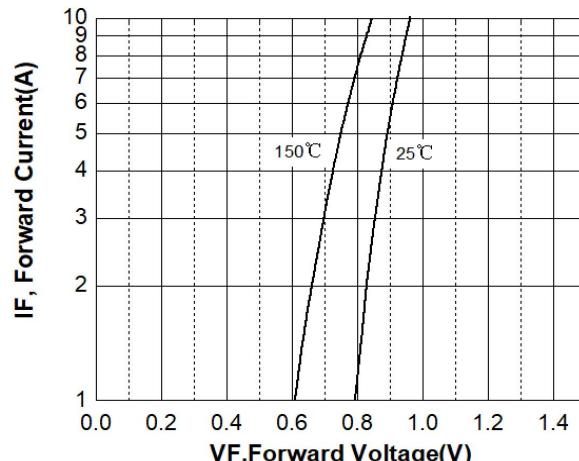


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

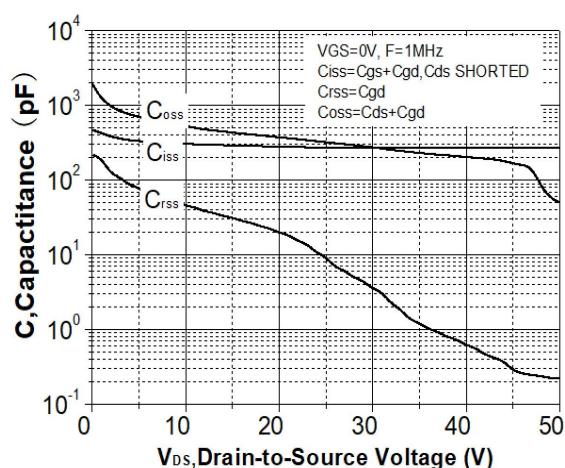


Figure 5. Capacitance Characteristics

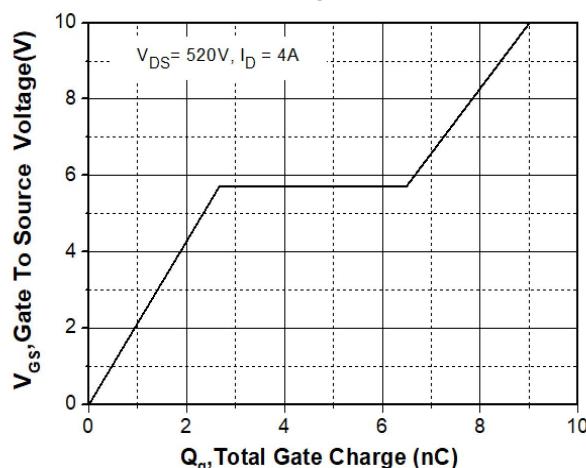
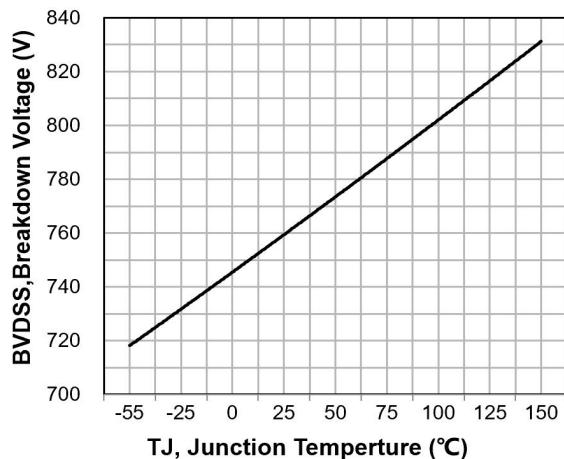
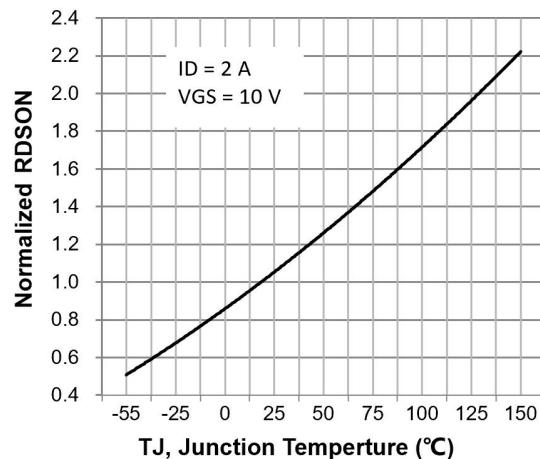


Figure 6. Gate Charge Characteristics

650 Super Junction Power MOSFET



**Figure 7. Breakdown Voltage Variation
vs Temperature**



**Figure 8. On-Resistance Variation
vs Temperature**

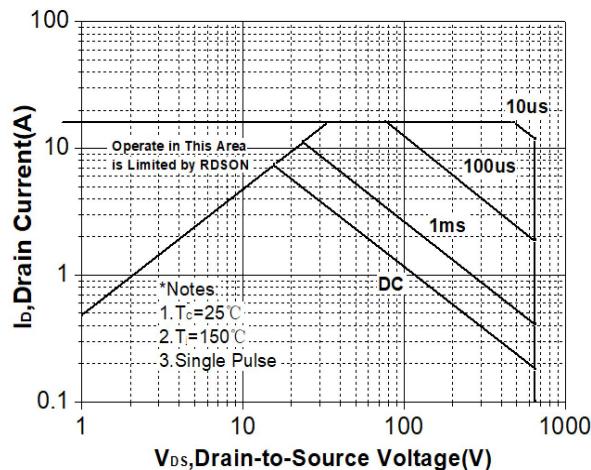
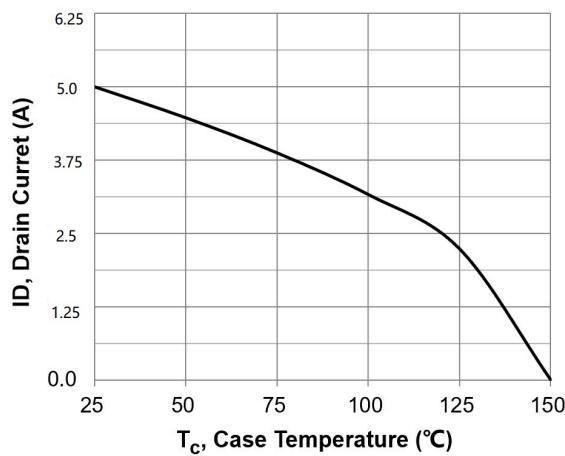


Figure 9. Maximum Safe Operating Area



**Figure 10. Maximum Drain Current
vs Case Temperature**

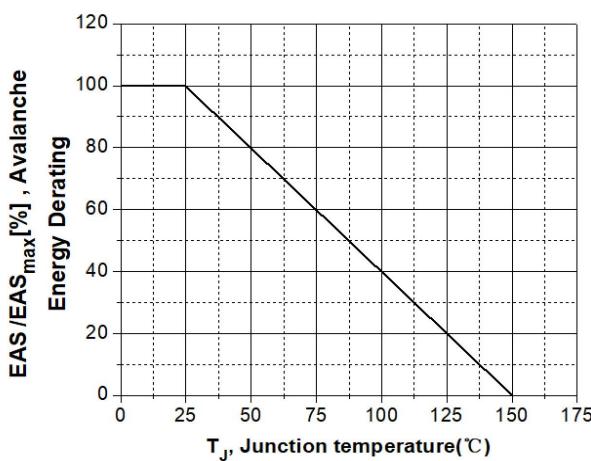
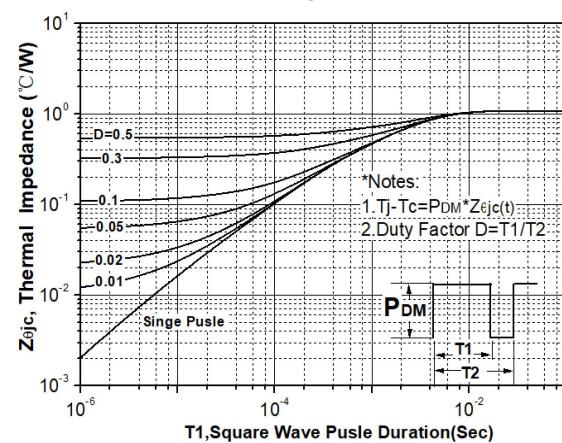


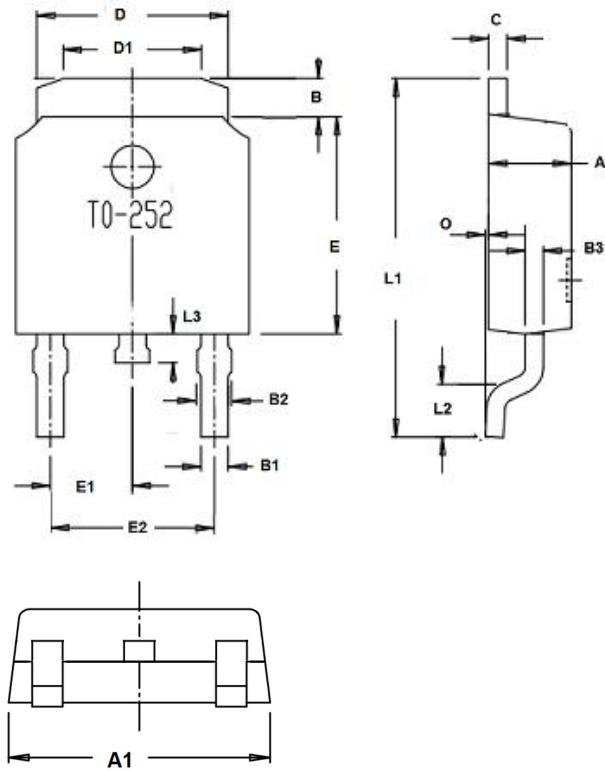
Figure 11. Transconductance vs. Drain Current



**Figure 12. Transient Thermal
Response Curve**

650 Super Junction Power MOSFET

TO-252 Package Outline Dimensions



Dim.	Min.	Max.
A	2.1	2.5
A1	6.3	6.9
B	0.96	1.42
B1	0.74	0.86
B2	0.74	0.94
C	Typ0.5	
D	5.33	5.53
D1	3.65	4.05
E	6.0	6.2
E1	Typ2.29	
E2	Typ4.58	
O	0	0.15
L1	9.9	10.5
L2	Typ1.65	
L3	0.6	1.0
All Dimensions in millimeter		